TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process)

2SA1382

Power Amplifier Applications
High-Speed Switching Applications

- High DC current gain: $h_{FE} = 150$ to 400 ($I_{C} = -0.5$ A)
- Low collector saturation voltage: $V_{CE (sat)} = -0.5 \text{ V (max) (IC} = -1 \text{ A)}$
- High-speed switching: $t_{stg} = 1.0 \mu s$ (typ.)

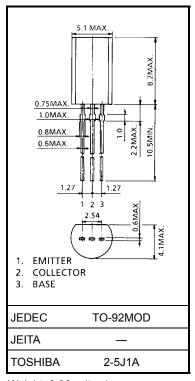
Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-base voltage		V _{CBO}	-50	V	
Collector-emitter voltage		V _{CEO}	-50	V	
Emitter-base voltage		V _{EBO}	-7	V	
Collector current	DC	IC	-2	А	
	Peak	I _{CP}	-4		
Base current		ΙΒ	-1	Α	
Collector power dissipation		PC	900	mW	
Junction temperature		Tj	150	°C	
Storage temperature range		T _{stg}	-55 to 150	°C	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in

Industrial Applications

Unit: mm



Weight: 0.36 g (typ.)

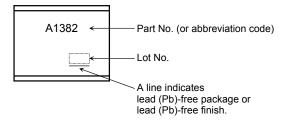
temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

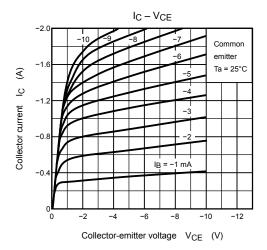


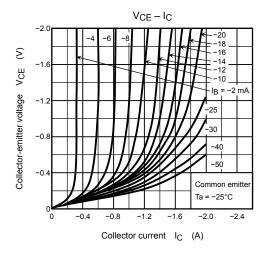
Electrical Characteristics (Ta = 25°C)

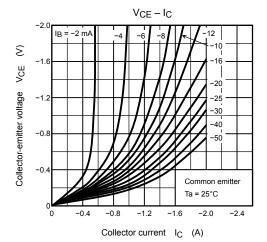
Chara	acteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off of	urrent	I _{CBO}	$V_{CB} = -50 \text{ V}, I_E = 0$	_	_	-0.1	μΑ
Emitter cut-off cu	rrent	I _{EBO}	V _{EB} = -7 V, I _C = 0	_	_	-0.1	μΑ
Collector-emitter	breakdown voltage	V (BR) CEO	I _C = -10 mA, I _B = 0	-50	_	_	V
DC current gain		h _{FE (1)}	V _{CE} = -2 V, I _C = -0.5 A	150	_	400	
		h _{FE (2)}	V _{CE} = -2 V, I _C = -1.5 A	60	_	_	
Collector-emitter	saturation voltage	V _{CE (sat)}	I _C = -1 A, I _B = -0.033 A	_	-0.2	-0.5	V
Base-emitter satu	ration voltage	V _{BE (sat)}	I _C = -1 A, I _B = -0.033 A	-	-0.9	-1.2	V
Transition freque	псу	f _T	V _{CE} = -2 V, I _C = -0.5 A	_	110	_	MHz
Collector output capacitance		C _{ob}	V _{CB} = −10 V, I _E = 0, f = 1 MHz	_	50	_	pF
Switching time Storage	Turn-on time	t _{on}	Output 20 μ s Input $ B_1 $ $ B_2 $ $ B_2 $ $ B_3 $	_	0.2	_	
	Storage time	t _{stg}		_	1.0	_	μs
	Fall time	t _f			0.2	_	

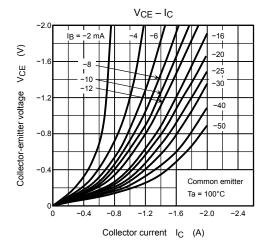
Marking

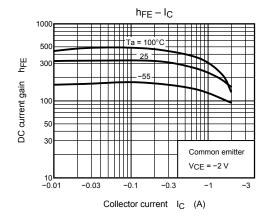


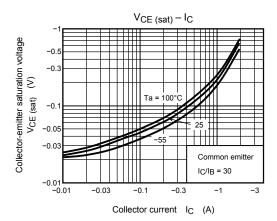




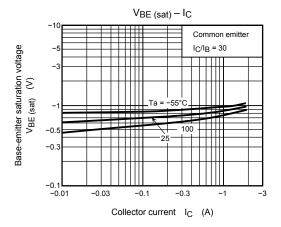


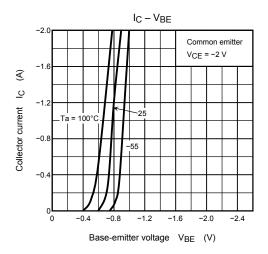


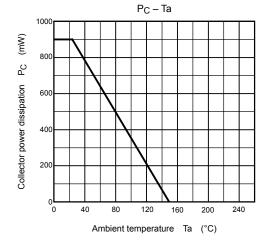


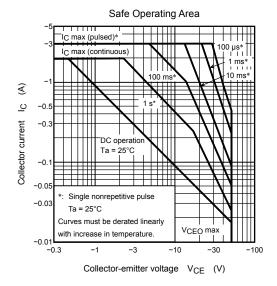


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